

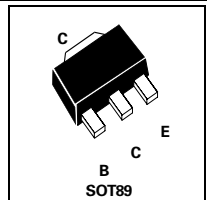
**SOT89 PNP SILICON PLANAR
HIGH VOLTAGE TRANSISTOR**

SXTA92

ISSUE 3 – JANUARY 1996

COMPLEMENTARY TYPE – SXTA42

PARTMARKING DETAIL – S2D



ABSOLUTE MAXIMUM RATINGS.

| PARAMETER | SYMBOL | VALUE | UNIT |
|--|----------------|-------------|-------------|
| Collector-Base Voltage | V_{CBO} | -300 | V |
| Collector-Emitter Voltage | V_{CEO} | -300 | V |
| Emitter-Base Voltage | V_{EBO} | -6 | V |
| Continuous Collector Current | I_C | -500 | mA |
| Power Dissipation at $T_{amb}=25^{\circ}C$ | P_{tot} | 1 | W |
| Operating and Storage Temperature Range | $T_j; T_{stg}$ | -65 to +150 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | CONDITIONS. |
|---------------------------------------|---------------|----------------|------|-------|---------|---|
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | -300 | | | V | $I_C=-100\mu A, I_E=0$ |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | -300 | | | V | $I_C=-1mA, I_B=0^*$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -5 | | | V | $I_E=-100\mu A, I_C=0$ |
| Collector Cut-Off Current | I_{CBO} | | | -0.25 | μA | $V_{CE}=-200V, I_E=0$ |
| Emitter Cut-Off Current | I_{EBO} | | | -0.1 | μA | $V_{EF}=-3V, I_C=0$ |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | | | -0.5 | V | $I_C=-20mA, I_B=-2mA^*$ |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | | | -0.9 | V | $I_C=-20mA, I_B=-2mA^*$ |
| Static Forward Current Transfer Ratio | h_{FE} | 25 40 25 | | | | $I_C=-1mA, V_{CE}=-10V^*$ $I_C=-10mA, V_{CE}=-10V^*$ $I_C=-30mA, V_{CE}=-10V^*$ |
| Transition Frequency | f_T | 50 | | | MHz | $I_C=-10mA, V_{CE}=-20V$ $f=20MHz$ |
| Output Capacitance | C_{obo} | | | 6 | pF | $V_{CE}=-20V, f=1MHz$ |

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$
For typical characteristics graphs see FMMTA92 datasheet.